แบบจำลองเชิงตัวเลขเพื่อจำลองการเปลี่ยนแปลงของความบกพร่องแบบจุดในโครงผลึก



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ขวัญชนก จันทร์สว่าง : แบบจำลองเชิงตัวเลขเพื่อจำลองการเปลี่ยนแปลงของความ บกพร่องแบบจุดในโกรงผลึก)( (NUMERICAL MODEL FOR SIMULATING POINT
 ชัย นิลสุวรรณโัมษต. 80 กน้า


การศึกษาคารเปลิยทเปลงขขดคความบกพร่องเบบขดในโครงผลึกโดยใช้แบบจำลอง เชิงตัวเลข เพื่อศึกบวคารเปลี่ยมเที่งของความบกพรจงต่อเวลา การศึกษาพบว่า เมื่อเกิดความ บกพร่องแบพจุดชนิดที่ว่างเคี่ยวขนนดน โครงผลึกแมนเฟสเซนเตอร์กิวบิคที่ภาวะสมดุล ค่าเฉลี่ย ของปริมาตรจำเหตะของอะตอมมีค่าเพิมขึ้นอย่างทันทีในช่วงเรก หลังจากนั้นมีค่าลดลง
 กรณีของความบคพร่องกบบดดในบริวฉมิดิอวกัน โดยมีำนวนนวามบกพร่องเพิ่มขึ้น มี จำนวนสูงสุดถึง 5 ดด ซึง ทำหนเกิดเป็นที่วางขนคดใหข่ขึ้น พบว่าการเปลี่ยนแปลงค่าเฉลี่ย ปริมาณจำเพาะของอะตอมอย่ามรวดเร้วในิช่วงแรคมีค่าใกลเเุยงกัน แต่ระบบที่มีจำนวนความ บกพร่องแบบจุดมากควาจะดดล่อยเข้ส์สมตุุใหม่เร็วคว่า และมีขนาดปริมาตรจำเพาะของ อะตอมใหญู่กว่ากรมีที่มีจำบวนทวววมมบกมร่องแบบจุดน้อยกว่า


## ศูนย์วิทยทรัพยากร


\#\#4871802521 : MAJOR NUCLEAR ENGINEERING
KEYWORDS : POINT DEFECT / CRYSTAL STRUCTURE / TRANSIENTS

KWUANCHANOK CHANSAWANG; NUMERICAL MODEL FOR SIMULATING POINT DEFECT TRANSIENTS. THESIS ADVISOR: ASSOC.PROF.SUNCHAI NILSUWANKOSIT,Ph,Q. $80^{\circ}$

A study on the dynamig of point defects in erystal structure was numerically conducted in order to obsepre their transients it was found that when a single vacancy defect ocourred in ah nitially perfect FCC-crystal structure, the average atomic volume was sudgenly inereased and then gradually-decreased down to the value close to the initial value. In case of mutiple vecancies at the same position with the number of vacancies/up to 5 , the results showed that the average atomic volumes at the heginning were very similar. However, the system with the higher number of point defects tended to approach the equilibrium faster and had the larger average atomic volume compared with the system with the lower number of point defects.


## ศูนย์วิทยทรัพยากร



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## CHAPTER I

## INTRODUCTION

### 1.1 Background and Problems of Interest

Solid materials are generally observed to have the crystal structure. The structure is made up of periodically repeating a structural building block, the unit cell. The pattern of ions or atoms within the crystal is described by the lattice. Atom or group of atoms attached at every lattice point is called the basis. The lattice and basis completely specify the crystal structure. The formation of the crystal is typically controlled by the valence elegtrons of the atoms that form the crystal. The strength, color and other physical properties are affected by the orystal structure.

Crystal is considered 'perfect crystal' when every atom stays in the correct position. This is the ideal condition which hardly exist. Every crystal contains lattice defects, or imperfections, which locally disrupt the ideal structure of the crystal. The general types of defects are point defects, line defects or dislocations and surface defects. Defects in the crystal structure can have a tremendous effect on a materials behavior, we can modify andimprove many of the physical, electrical, magnetic, and optical properties of crystal materials by controlling imperfections in their lattice structure. So, in many fields of science and engineering are largely concerned with how
such lattice defects are formed, how they interact with each other, and how they affect
macroscopic properties. [1] Both experiments and simulations are widely developed. Various experimental designs can show the appropriate results which are beneficial in many
areas, ibut have the limitationsuin some-conditions. On the other side, simulation can often come very close to experimental conditions, to the extent that computer results หาลงกรณมหาวิทยาลย experiments at the microscopic level, but also to study regions which are not accessible experimentally, or which would imply very expensive experiments, such as under extremely high pressure.

The scale of simulation in computational crystal materials is vast, hierarchical models begin from nano-scale (characteristic length $\sim 10^{-9}-10^{-7} \mathrm{~m}$.), microscale (characteristic length $\sim 10^{-8}-10^{-6} \mathrm{~m}$.), meso-scale (characteristic length $\sim 10^{-7}-$ $10^{-4} \mathrm{~m}$.), and macro-scale (characteristic length $\geq 10^{-3} \mathrm{~m}$. .). Most of simulation must be connected with appropriate scale but these make limitation in them.

The motivation of this dissertation is trying to understand the dynamics of lattice defects, specifically the transient of this system. The first objective aims to create a computer program to calculate the energy term, especially potential energy function. The reason for focusing on potential energy function is the behavior of lattice defects that atoms interact with each other. These interactions originate forces which action of these instantaneous forces. As the atoms move their relative positions change and forces change as well. Forces are usually obtained as the gradient of a potential energy function, depending on the positions of the particles. The second objective aims to analyse the patterns of lattice defects and predict the possible final states of the transients.
1.2 Thesis Objective


1. To develop a computer program for simulating point defect transients.

2. To predict the possible final states of the transients and/or the time in which a transientmay require to reach its final state. 1.3 Scope of Work

3. Various initial conditions for single and multiple defects will be attempted.
4. The obtained results are to be compared with the available data obtained from the experiments and/or from the theoretical prediction.

### 1.4 Expected Benefit

Obtain the computer program for simulating the transient of lattice defects. The program will be used as a/tool in which further study and the analysis on the formation of the lattice and the propagation of their defects can be conducted.


1. In 1997 [2], Furio Ercolessi presented 'A molecular dynamics primer' that summarize the skeleton for a short hands-on course on molecular dynamics. These notes showed that in the past, interactions were obtained by two-body potentials with simple analytical form, such as Morse or Lennard-Jones (since 1957). After that, the most accurate potentials contain many-body terms and are determined numerically by reproducing as closely as possible forces predicted by first-principle methods (since 1985). Also explained about limitations of molecular dynamics when deal with the system at the atomistic level, everybody knows this level obey quantum laws rather than classical laws. A simple test of the validity of the classical approximation is based on

where $M$ is the atomic mass and $T$ is the temperature. The classical approximation is justified if $\Lambda<a$, where $a$ is the mean nearest neighbor separation. If one considers
for instance liquids at the triple point, $\Lambda / a$ is of the order of 0.1 for light elements such as Li and Ar , decreasing further for heavier elements. The classical approximation is พาลงกรถมมหาวิทยาดย crystals below the Debye temperature, or the anomalous behavior of the thermal
expansion coefficient, are well known examples of measurable quantum effects in solids. Molecular dynamics results should be interpreted with caution in these regions.

These notes also emphasized that the realism of the simulation depends on the ability of the potential chosen to reproduce the behavior of the material under the conditions at which the simulation is run.
2. In 2000 [3], Merimaa, L.F. Perondi and K. Kaski introduced an interactive simulation program illustrating grain boundary and fracture phenomena in solids. The dynamical behavior of a two-dimensional Lennard-Jones model system under stress, with either a grain poundary or an initial crack, is simulated through a molecular dynamics algorithm. All parameters defining the system and the dynamical load are set through a graphical user interface. A run-time representation of the system is displayed on a graphics window, which has been endowed with magnification and other visualization aid tools. The program runs, on a UNIX-X11 Window System platform. The graphical part relies on the MOTIF library. The program has been devised for illustrative purposes. It displays the main elements of an interactive simulation and may be regarded as giving an illustration of the concept of interactivity.

3. In 2002 [4], L.E. Shilkrot, W.A. Curtin and R.E. Miller introduced a method for reducing the degree of freedom in simulations of mechanical behavior of materials without sacrificing important physics. The method essentially combines the quasicontinuth (QC) method with continuum defect models such as the discrete dislocation (DD) method. A procedure for the 'passing' of dislocation defects from the atomistic to the continuum description in 2 d problems is also presented. The overall 2 d method with dislocation defects is validated by comparing the predictions of the
coupled model to 'exact' fully atomistic models for several equilibrium dislocation geometries and a nanoindentation problem in aluminum, and excellent agreement is จุฬาลงกรณมมหาวิทยาลัย interatomic forces in materials based on the ideas of density functional theory and the variational principle, without details of the mathematics involved. Also explain that ionic
materials and simple metals, arguments based on electrostatics and linear response have a firm foundation in quantum mechanics, and are key elements for making simplified models. In other materials, he showed that it is possible to simplify the manybody theory to such an extent that useful analytic models emerge.
5. In 2004 [6], W.K. Liu et al briefly, reviewed the essential tools used by nanoscale researchers. These simulation methods include the broad areas of quantum mechanics, molecular dynamics and multiple-scale approaches, based on coupling the atomistic and continetum models. They conclusively demonstrated that the atomistic simulation tools themselyes are not sufficient for many of the interesting and fundamental problems that arise in computational mechanics, and that these deficiencies lead to the thrust of multiple-scale methods. They also summarized the strengths and limitations of currently available multiple-scale techniques, where the emphasis is made on the latest perspective approaches, such as the bridging scale method, multi-scale boundary conditions, and multi-scale fluidics.

In detail of this paper showed that nanoscale materials will be used in conjunction with other components that are larger, and have different response times, thus operating at different time and length scales. Single scale methods such as 'ab initio' quantum mechanical methods or molecular dynamics (MD) will have difficulty in analyzing such hybrid structures due to the limitations in terms of the time and length scales that each method is confined to. Because of the avajlability of accurate interatomic potentials for a range of materials, classical MD simulations have become prominent as atool for elucidating complex physical phenomena.

The paper's outline is given by the following. Section 2 reviews the fundamentals of classical molecular dynamic simulations, such as the Lagrangian and
Hamittonian formulations, and the structure of interatomic potential functions. Section 3 informs the reader on the relevant quantum mechanicalapproaches and explains the developing the coupled multi-scale methods. Section 5 reviews available multi-scale approaches: hierarchical and concurrent coupling of the atomistic and continuum
simulations (with the emphasis on the bridging scale method), multi-scale boundary conditions and multiple-scale fluidics. Section 6 concludes the paper by discussing future research needs in multiple-scale analysis.

This paper also introduced for such systems, the computer-aided engineering tools must be able to span length scales from nanometers to microns, and time scales from femtoseconds to micro-segonds. Therefore, these systems cannot be modeled by continutum methods alone, because they are too small, or by molecular methods alone, because they are too large. And in supporting the design and qualification of nanostructered materials, a range of simulation tools must be available to designers justas they are today avalable at the macroscopic scales in general purpose software.
6. In 2004 [7][8][9], Teik-Cheng Lim proposed the study of potential energy function in various pappers, in particular the connection among classical interatomic potential functions, these papers showed the relationship among the classical functions of Lennard-Joneds, Morse, Rydberg and Buckingham potential, followed by relationships between the classical pair potentials of Morse and Buckingham with the 2-body portion of other empirical potentials, such as BiswasHammann and Bauer-Maysenholder-Seeger. The results showed imposing equal potential energy, and their first two derivatives at equilibrium as well as the usage of calculus and Maclaurin series expansions.

In 2007 [10], M. Patriarca et al. proposed the study of crystal defects
and the complex processes underlying their formation and time evolution has motivated the development of the program ALINE for interactivellolecular dynamics experiments. They showed that ALINE couples a molecular dynamios code to a Graphical User Interface and runs on UNIX-X11 Window System platform with the MOTIF library, which and user-friendly framework for numerical experiments, in which the main parameters can be interactively varied and the system visualized in various way. They illustrated the main features of the program through some examples of detection and dynamical
tracking of point-defects, linear defects, and planar defects, such as stacking faults in lattice-mismatched heterostructures.


## CHAPTER II

THEORETICAL BACKGROUND

### 2.1 Defects of Crystal Structure[11]

Every crystal contains lattice defects, or imperfections, which locally disrupt the ideal structure of the crystal. Defects come in several types and are often classified according to the number of spatial dimensions which is required to geometrically describe them. Their prēsence affects physical properties of the crystal and lead to various phenomena

### 2.1.1 Point Defects

In a perfect lattice all atoms are located at specific lattice sites (ignoring thermal motion). There are two possible point defects, namely vacancies and interstitials. A vacancy is an unoccupied lattice point, while an interstitial is an atom located at a non-lattice site. For each fixed temperature there is an equilibrium concentration of vacancies in a crystal. In many common metals the fraction of vacant lattice sites just below the melting temperature is of the order of $10^{-4}$ to $10^{-3}$. The equilibrium concentration of interstitials near the melting temperature is expected to be of the order of magnitude smaller than that of the equilibrium concentration of vacancies.
 defects. There-are two type: substitutional (an atom of a kind different from the host atoms occupying a lattice site) and interstitial (an atom of a kind different from the host


Fig. 2.1 (a) Vacancies and Self-interstitials, (b) and (c) Substitutional [11]

Point defects influence many physical properties of metals. For example, atoms surrounding a vacant lattice site are more loosely bound than those in a perfect lattice. The forces between the atoms thus are weakened (i.e. the vibrational frequencies are lowered) giving an increased vibrational entropy because the lattice is more compressed in the vicinity of an interstitial. Point defect mechanisms dominate in self-diffusion processes. Vacancies cause an increase in the volume of a crystal, and hence contribute to the thermal expansion. The enthalpy and heat capacity increase due to point defects

The formation of point defects in Solids was first predicted by Frenkel in 1926. At high-temperatures the thermal vibrations of the atoms may cause an atom to leave its equilibrium lattice site and oecupy an interstitial position in the lattice. In this mechanism a vacancy and an interstitial are created simultaneously, and are referred to as a Frenkel defect. In 1930, Wagner and Schottky demonstrated a way for the creation of vacancies: an atom leaves its lattice site and occupies an available position at the surface of the crystal or at internalimperfections in the crystal such as dislocations, grain boundaries, or inclusions, (Fig. 2.2). This mechanism dominates in metals with close-packed structure where the formation energy of vacancies generally is much lower than the formation energy of interstitials. Experimental measurements of vacancy concentrations often rely on the influence of vacancies on thermophysical properties, e.g. thermal expansion and electric resistivity. The problem is to separate the effect of vacancies from other effects, e.g. anharmonicity. Differential dilatometry measures the vacancy concentration directly. In such experiments the linear thermal expansion coefficient and the change in the lattice parameter with temperature are measured simultäneously. From then differencen between those quantities the vacancy
concentration can be deduced. The equilibrium concentration of interstitials can be determined using elastic constants measurements.

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Fig. 2.2 Frenkelimperfectionand Schottky imperfection [11]
2.1.2 Line Defects or Dislocations

Imagine that the bonds between the atoms in a simple cubic lattice are represented by flexible springs. If all bonds intersected by a plane which goes through non-atomic sites were instantaneously broken, the lattice would separate along this line if pulled in tension. A screw dislocation is introduced by displacing the two faces of such a cut relative to each other. If instead an extra atomic plane would be placed between the faces, an edge dislocation is created. In a real crystal, dislocations may have characteristics of both edgé and screw type, (Fig. 2.3).


Fig. 2.3 (a) Screw dislocations, (b) Edge dislocations [11]

Dislocations have high formation energy and are not thermally generated at normal temperatures. However, dislocations are introduced through mechanical deformation even at intermediate temperature. The dislocation density is defined as the total length of dislocations per volume. In a carefully treated metallic crystal this value can be as low as $10^{-2} \mathrm{~cm}^{-2}$. It increases rapidly with plastic deformation, and typical value for a heavily deformed metal is $15 \times 10^{10} \mathrm{em}^{-2}$ The dislocation density in metallic crystals generally is higher than in non-metallic crystal's. Thus, dislocations may become important at high temperatures, and are essential in understanding the deformation of materials. They account for the difference, by many orders of magnitude, between measured critical shear stresses of crystals and theoretical estimations.

Theidea of dislocations dates from the end of the 1920s. In 1934 Orowan, Polanyi, and Taylor in simultaneous independent papers laid the foundations of the modern dislocation theory of /slip, although the concept of dislocations had been introduced some years earlier. The firstmajor review of the dislocation theory of crystals was written by Seitz and Read (1941), and later by Cottrell (1949). At the end of the 1960s, much of the modern theory of dislocations had been completed. The geometrical and elastic propenties of dislocations, the theory of plastic deformation, and the role of dislocation theory in-explaining crystal growth, were developed. There are many techniques for the deteetion of dislocations in crystals, e.g. X-ray diffraction, 2.1.3 Planar Defects : Stacking faults

Perfect lattices can be described as a stacking of identical atom layers arrangedain a regular sequence. $9^{\text {There may }}$ me one or several ways to position one
layer on top of another. In a face-centered cubic lattice there are two ways in which closelpacked planes (the (111) planes) can be placed on top of each other. The จุหาลงครรณ์มม่าวิทยาวลัย

Stacking faults play an important role in materials science because of their interaction with dislocation. They can be visualized by electron diffraction. Dislocations
often split into partial dislocations (in face-centered cubic metals), which are connected by a stacking fault. The stacking fault energy, $\boldsymbol{\gamma}$ is the energy required to introduce a stacking fault in a crystal. It is directly related to, e.g. the dissociation of a dislocation into two partials. Calculations of the stacking fault energy have been carried out using classical simulations and ab-initio methods. Using isotropic elasticity theory, the splitting distance, $d_{\text {split }}$ between two , partial dislocations can be calculated, from which $d_{\text {split }} \approx \gamma^{-1}$. The relation between $y$ and $d_{\text {split }}$ may be used in experimental determinations of the stacking fault energy
 diameters, they can exert attractive forces on each other. But if the atoms are so close to each other that their electron shells overlap, the forces between the atoms are repulsive.

Between these limits, there can be an equilibrium separation distance at which two atoms form a molecule. If these atoms are displaced slightly from equilibrium, they will oscillate.

As an example, consider one type of interaction between atoms called the van der Waals interaction. Let the center of one,atom be at the origin, and let the center of the other atom be a distance $r$ away; the equilibrium distance between centers is $r=R_{0}$. Experiment shows that the van der Waals interaction can be described by the potential energy function $\left.U=U_{0}\left(\frac{R_{0}}{\bar{r}}\right)^{12}-2\left(\frac{R_{0}}{r}\right)^{6}\right]$, (3-2)
where $U_{0}$ is a positive constant with units of joules. If two atoms are very far apart, $U=0$; if they are separated by the equilibrium distance $r=R_{0}, U=-U_{0}$. The force on the second atom is the negative derivative of Eq. (2.1),

$$
F=-\frac{d U}{d r}=U_{0}\left[\frac{12 R_{0}^{12}}{r^{13}}-2 \frac{6 R_{0}{ }^{6}}{r^{7}}\right]
$$

is a restoring foree


To study small-amplitude oscillations around the equilibrium separation


$$
\begin{align*}
F & =12 \frac{U_{0}}{R_{0}}\left[\left(\frac{R_{0}}{R_{0}+x}\right)^{13}-\left(\frac{R_{0}}{R_{0}+x}\right)^{7}\right] \\
& =12 \frac{U_{0}}{R_{0}}\left[\frac{1}{\left(1+x / R_{0}\right)^{13}}-\frac{1}{\left(1+x / R_{0}\right)^{7}}\right] . \tag{2.3}
\end{align*}
$$

This looks nothing like Hooke's law, $F=-k x$, so we might be tempted to conclude that molecular oscillations cannot be simple harmonic motion. But let us restrict ourselves to small-amplitude oscillations so that the absolute value of the displacement $X$ will be small in comparison to $R_{0}$ and the absolute value of the ratio $x / R_{0}$ will be much less than 1. We can then simplify Eq. (2.3) by using the binomial theorem:

$$
\begin{equation*}
(1+u)^{n}=\frac{n(n-1)}{1+n u+\frac{n(n-1)}{}(n-2)} 3!u^{2}+\frac{n!}{+\frac{n}{3}} u^{3}+\cdots \tag{2.4}
\end{equation*}
$$

If $|u|$ is much less/than 1, each successive term in Eq. (2.4) is much smaller than the one it follows, and we can safely approximate $(1+u)^{n}$ by just the first two term. Th Eq. (2.3), $u$ is replaced by $x / R_{0}$ and $n$ equals -13 or -7 , so


This is just Hooke's law, with force constant $k=\frac{72 U_{0}}{R_{0}{ }^{2}}$, (Note that $k$ has the correct units, $\mathrm{J} / \mathrm{m}^{2}$ or $\mathrm{N} / \mathrm{m}$.) So oscillations of molecules bounded by the van der Waals interaction can be simple harmonic motion, provided that the amplitudesis small in comparison to $R_{0}$ so that the approximation $\left|x / R_{0}\right| \ll 1$ used in the derivation of Eq. (2.5) is valid.
 constant to the potential energy has no effect on the physics, so the system of two
atoms is fundamentally no different from a mass attached to a horizontal spring for which $U=\frac{1}{2} k x^{2}$.

### 2.3 Molecular Dynamic Simulation [13],[14]

### 2.3.1 Potential Energy Function in Classical Molecular Dynamics Simulation

One of the objectives of this dissertation is to simulate the transient of lattice defects. In-order to do so requires an understanding on the dynamics of lattice defects; the position, the velocity, the acceleration. The dynamics can be explained through the Hamiltonian equations of motion. The equations represent the energy of the physical system, that is, the sum of kinetic and potential energy. An alternative description, the terms of the generalized coordinates and momentum, is also utilized within the Hamiltonian formulation.

The complete differential of the Lagrangian function reads

where


We can rewrite this differential as


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The right-hand side of Eq. (2.7) can be rearranged as

$$
\begin{equation*}
d L=\sum_{i} \dot{p}_{i} d q_{i}+d\left(\sum_{i} p_{i} d \dot{q}_{i}\right)-\sum_{i} \dot{q}_{i} d p_{i} \tag{2.9}
\end{equation*}
$$

$$
\begin{equation*}
d\left(\sum_{i} p_{i} \dot{q}_{i}-L\right)=\sum_{T} \dot{q}_{i} d p_{i}-\sum_{i} \dot{p}_{i} d q_{i} \tag{2.10}
\end{equation*}
$$

where the function
s referred to as the Hamiltonian of the system. The value of the Hamiltonian function is an integral of motion for conservative system, and it is defined to be the total energy of the system in terms of the generalized coordinates and momenta. Thus, we have obtained



These are the Hamiltonian equations of motion in terms of new variable $p$ and $q$.


Eor a conservative system of $N$ interacting atoms in a Cartesian coordinate system, the Hamiltonian description acquires the following form:

Q $9 \%$ wherethemomentalare relatedtothe racius vecters as $p_{i}=m_{i} r_{i} \dot{r}_{i}=\frac{\partial H}{\partial p_{i}}$,

If the Hamiltonian function and an initial state of the atoms in the system are known, one can compute the instantaneous positions and momentum of the atoms at all successive times that gives the dynamic evolution of the system.

Unlike the positions and momentum which can be computed quite easily from Hamiltonian function, the potential energy terms turns out to be difficult. The potential energy function is an extremely complicated object, when accurately representing the atomic interactions within the simulated system.


In a model for atomic interaction, the form of potential energy function for various systems is produced, the general structure of this function is presented by the following:

where $r_{n}$ is the radius vector of the $n$th particle and function $V_{m}$ is called the $m$-body potential. The first term represents the energy due to an external force field, such as gravitational-field or electrostatic field into which the system is immersed. The second term shows pair-wise interactions of the particles. The third tern-gives the three-body components. in practice, the external field term is usually ignored, while all the multibody effects are incorporated into $V_{2}$ in order to reduce the computational expense of the simulations.
 classical molecular dynamics simulation. Among them are these two popular models to describe


$$
\begin{equation*}
r=\left|r_{i j}\right|=\left|r_{i}-r_{j}\right| \tag{2.17}
\end{equation*}
$$

where $r_{i j}$ is the interatomic radius-vector, $\sigma$ is the collision diameter, the distance at which $V(r)=0$, and $\varepsilon$ shows the bonding/dislocation energy. The first term of this potential represents atomic repulsion and the second term shows attraction between two atoms.

where $\rho$ and $\mathcal{E}$ are equilibrium bond length and dislocation energy respectively; $\beta$ is an inverse length scaling factor. The first term of this potential is repulsive whereas the second term is attractive and is interpreted as a representation of bonding. Morse potential has been adapted for modeling atomic interaction in various types of materials and interfaces.

The $L J$ and Morse potentials are most commonly used in molecular dynamics simulations, in chemistry, physics and engineering. They describe multi-body


Fig. 2.5 Pair-wise potentials and the interatomic forces (a) LJ, (b) Morse.[6]

Tersoff potential [6],[15] for a class of covalent system reads as

$$
\begin{equation*}
V_{i j}=f_{c}\left(r_{i j}\right)\left(A e^{-\lambda_{1} r_{i j}}-B_{i j} e^{-\lambda_{2} r_{i j}}\right) \tag{2.19}
\end{equation*}
$$

where $f_{c}$ is the cutoff function. If the local bond-order is ignored, so that $B=2 A=$ const., and $\lambda_{1}=2 \lambda_{2}$, then potential reduces to the Morse model.

Not only used to describe the pair-wise atomic interactions, but also the multi-body interaction, Brenner potential and Reactive Empirical Bond Order (REBO) potential [6],[16] is extended from the Tersoff model to account for different types of chemical bonds that occur in the diamond and graphite phases of the carbon, as well in hydrocarbon molecules.

There is another special form of the multi-body potential:

Embedded atom method (EAM),[6],[10]: for metallic system


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## CHAPTER III

## SPRING-MASS MODEL

### 3.1 Description of the Model

Using the concept of Hamiltonian, the general structure of potential energy function, and the revision of the vibration of molecules in CHAPTER II, we are ready to investigate the simplest model representing the system of atomic interaction namely the model of spring. (Fig.3. 1)



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$$
\begin{equation*}
V=\sum_{i=1}^{m} \frac{1}{2} K\left(\Delta l_{i}\right)^{2}, \tag{3.2}
\end{equation*}
$$

where

$$
\begin{equation*}
\Delta l_{i}=\left|\overrightarrow{r_{\alpha}}-\overrightarrow{r_{\beta}}\right|-L \tag{3.3}
\end{equation*}
$$



$$
\begin{align*}
& F_{n x}=-\frac{\partial H}{\partial x_{n}},  \tag{3.7}\\
& 0  \tag{3.8}\\
& \frac{\partial H}{\partial z_{n}} \text {. } \tag{3.9}
\end{align*}
$$

That is,

$$
\begin{equation*}
F_{n x}=-\sum_{i=0}^{m}\left\{K \cdot \frac{\left(\left|\overrightarrow{r_{\alpha}}-\overrightarrow{r_{\beta}}\right|-L\right)}{\left|\overrightarrow{r_{\alpha}}-\overrightarrow{r_{\beta}}\right|} \cdot\left(x_{\alpha}-x_{\beta}\right) \cdot \frac{\partial}{\partial x_{n}}\left(x_{\alpha}-x_{\beta}\right)\right\} . \tag{3.10}
\end{equation*}
$$


numerical integrator [14],[17]. Let the problem be specified as follows, จุหาลงกรส์มูหาวิทยาลัย

Then the RK4 method for this problem is given by the following equations:


## 

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Hamiltonian is then calculated. The force is computed in two ways; one is through Eq.
(3.10-3.12) by formula method, and the other is through Eq. (3.13) by numerical method.

We divide the force by mass to obtain the acceleration. After that, we use the RK4 to solve the integral form to take the velocity, and finally the new position. Hamiltonian is calculated and these new positions are stored to the new configuration in the next time


Fig. 3.2 Flow chart of the spring model

### 3.2 Case Study on Simple Cubic Crystal

The model observes the system of simple cubic $3 \times 3 \times 3$. The description of the system is set as shown in the table:

Table 3.1 The description of the system; simple cubic $3 \times 3 \times 3$.


Atom no. 13 is displaced-from the coordinate $(1.0,1.0,1.0)$ to $(1.1,1.1,1.1)$.
 Hamiltonian at each time step. In calculation the forces acting on the atoms based on
method. The other was to obtain the derivative numerically. This was labeled as the $H$ -
numerical method. The results obtained with these two methods were compared with the initial Hamiltonian $\left(H_{0}\right)$ as shown in Fig. 3.3.
 with time are shown respectively in the Fig. 3.4-3.6


The position of the atom no. 13 varies around the equilibrium state that shows the vibration of the atom in the system. The value of position of atom no. 13 in each axis versus time by both methods is the same value until the run time is about 700 . This means that the numerical method in this model can show the exact value in limited run time. Therefore, making an adjustment of the differential step is needed for decreasing different value, but that will make more/longer time simulation usage.
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Fig. 3.6 Position of atom no. 13 in $Z$ axis

## CHAPTER IV

## SIMULATION ON POINT DEFECT FOR FCC STRUCTURE

### 4.1 Simulation of Point Defect with ALINE

In CHAPTER IIt, although it is clear that the model can accurately provide the results from calculation based on the Hamiltonian in order to simulate of the atom vibration in a simple cubic crystal, there still are some limitations in crystal system and particularly in terms of time usage of simulation

the numerical program ALINE which was written with the same concept was implemented. The ALINE program is strongly effective in simulating point defects in FCC crystal system. Thus, the program has been implied in this research to study the dynamics of point defects as well as the transients of the system.

ALINE (Atomic Laboratory for Interactive Numerical Experiments) is a three-dimensional interactive moleculan dynamics program designed to simulate dynamics of the defects in the crystalline structure. This program couples a molecular dynamics code to a Graphical UserInterface and runs on a UNIX-X11 Window System platform with the MOTIF library, which contained in many standard Linux releases. ALINE provides an effective and user-friendly framework for numerical experiments, in which the mainparameters can be interactively varied and the system visualized in various ways. , this program is suitable for the problem of interest in this study.

through a pair-wise Lennard-Jones (LJ) potential or a many-body EAM potential,

$$
\begin{equation*}
E_{p}=\frac{1}{2} \sum_{i \neq j} W_{i j}\left(r_{i j}\right) \tag{4.1}
\end{equation*}
$$

where $r_{i}=\left|r_{i}(t)-r_{j}(t)\right|$ is the distance between particles $i$ and $j$ located at $r_{i}(t)$ and $r_{j}(t)$. To improve the performance of simulations without affecting considerably the dynamics of the system, an interaction cut-off $r_{C}$ is introduced and the cell method used for computing the interatomic forces. The functional form of the $L J$ potential used is modified as foHows,

$$
\begin{align*}
& \text { sed is modified as foHtows, }  \tag{4.2}\\
& W_{i j}(r)= \begin{cases}V_{i j}(r) \\
0,\end{cases}
\end{align*}
$$

Where $V_{i j}\left(r_{c}\right)=\left[\partial V_{i j}(r) / \partial r\right]_{r=r_{c}}$, while $V_{i j}(r)$ represents the unperturbed LJ potential, the

$$
\begin{gather*}
(2.17)=\left(\frac{\beta}{(\beta)}\right. \\
V_{i j}(r)=4 \varepsilon_{i j}\left[\left(\frac{\sigma_{i j}}{r}\right)^{12}-\left(\frac{\sigma_{i j}}{r}\right)^{6}\right] \tag{4.3}
\end{gather*}
$$

where $\varepsilon_{i j}$ and $\sigma_{i j}$ representithe energy and length scales, respectively, of the interaction potential between the $i^{\text {th }}$ and the $j^{\text {th }}$ particle. The corresponding potential minimum is $V_{i j}=-\varepsilon_{i j}$ at $\bar{\sigma} 2^{1 / 6} \sigma_{i j}$. The parameter $\varepsilon_{i j}$ and $\sigma_{i j}$ may be different depending on the particle types and are assumed to be related to those of particles $i$ andj as $\varepsilon_{i j}=\sqrt{\varepsilon_{i i} \sigma_{j j}}$ and $\sigma_{i j}=\sigma_{i i}+\sigma_{j j}$. The last two terms on the right-hand side of Eq. (4.2) represent correction terms which make the potential and its first derivative continuous at the cut-off $r=r_{C}$. It is to bel noticed that Eq. (4.2) represents a potential with functional form different from that of the original LJ potential, the equilibrium distance and the potenfial minimum may differ appreciably if $r_{c}$ is
chosen too small. Thus, the potential parameters $\varepsilon_{i j}$ and $\sigma_{i j}$ are properlydrescaled at the beginning of the run in order to preserve the original values of the potential minimum and equilibrium distance for the unperturbed LO potential. All the $D$ parameters $\varepsilon, \sigma$,
and $r_{c}$ are now the basic inputparameters, which can befixed by the user and are by default assigned the rescaled values $\varepsilon=1, \sigma=1$, and $r_{c} / \sigma=2.5$, while the equilibrium lattice constant $a$ is computed by minimizing the interaction energy with the
neighbors. This does not create big problems because it is expected that if $\sigma$ is of the order of unity, also the lattice constant $a$ will be of the same order of magnitude. For time scale, in ALINE used time step, $d t=0.01$.

In general, the material of the study was presumed to have FCC type structure. The kind of atoms on ions that formed the basis of the structure was not specified. While this could have large effect on the length and time scale of the transient, the pattern in which the transient proceeded which was of major interest should be less affected.

For the simulations, the lattice constant was presumed to have the value of unity and the periodic condition was used for the boundary condition. Four cases of simulations were attempted on single vacancy. The volumes of these systems were initially containing (a) 2000 atoms, (b) 6750 atoms, (c) 16000 atoms and (d) 31250 atoms. In each case, only one atom at the center of the system was assumed to be missing when the simulation was initiated. Then the multiple vacancies (2-, 3-, 4-, and 5atoms) were observed in system of 2000 atoms. With the periodic boundary, the different number of atoms contained in the system then in turn identified the defect
4.2
 by one atom, it was necessary to count the number of atom dontained in a given small volume, subsystem, and then to divide it by the volume. It should be noted that if the subsystem was too smail, the number of atoms contained could be varied very widely. On the other hand, if the subsystem was too large, then the significant of difference in number of atoms then might be lost. It was therefore necessary to choose the

Since ALINE produced the output which described the positions of atoms at the different time step, by specifying the subsystem as described in Fig. 4.1, it was then possible to count the number of atoms contained in each subsystem.


Fig. 4.1 System of length $L_{x}$, width $L_{y}$ and height $L_{z}$ was divided in to subsystems,
 information regarding the number of subsystems containing the same number of atoms was obtained and the frequency distribution was created. With $i$ being the specific Case where the number of atom $n_{i}$ in the subsystem was counted and $f_{i}$ being the number of such subsystems, the average atomic volume $V_{m}$ was calculated as

$$
\begin{equation*}
V_{m}=\frac{\sum_{i} f_{i} \frac{B_{x} B_{y} B_{z}}{n_{i}}}{\sum_{i} f_{i}} \tag{4.4}
\end{equation*}
$$

It should be noted that $\sum_{i} f_{i}$ was the total number of subsystems and $\sum_{i} f_{i} n_{i}$ was the total number of atoms contained in the whole system.
4.4 Variation of Average Atomic Volume with Number of Divisions

From the results/obtained from ALINE, transformed to 'dat' files, containing the value of $x, y$, and $z$ coordinates, the box-counting model was used and the average atomic volume was calcułated. As it was necessary to identify the suitable size of subsystem which would have allowed for the calculation of the average atomic volume that was both stable (was not widely varied by the number of subsystems ) but still sensitive to the change in number of atoms that were moving in and out of the subsystems. To consider for the suitable size, the counting obtained with different number of subsystems $\left(n_{d}^{3}, n_{d}\right.$ was the number of divisions in each axis ) were obtained and the related average atomic volume were calculated as shown in Fig. 4.24.5

## $\underline{\underline{120} 5+5151}$

From Fig. 4.2-4.5, the very large value of $n_{d}$ in every case resulted in the very smallaverage atomic volume. This was because the agtual volumes of the subsystems in दhese cases were so small such that they would either contain only one atom or not at all. This condition highly distorts and under estimated the average atomic volume. On the other hand, with the very low number of $n_{d}$, the subsystems became large such that the change in number of atoms it contained could be insignificant. It
was of interest that a peak in the average atomic volume curved was observed in every case. It was tempting to assumed that the value of $n_{d}$ associated with such peak gave หาดงกรถมมหาวิทยาลย initial atoms of (a) 2000, (b) 6750, (c) 16000 and (d) 31250 were respectively associated with the arrangement of 2 structure sets; (a) $10 \times 10 \times 10$, (b) $15 \times 15 \times 15$, (c) $20 \times 20 \times 20$ and
(d) $25 \times 25 \times 25$. As a result, in each case, the value of $n_{d}$ that was a common denominator to such arrangement should be avoided. This was because it gave the subsystems that coincided with the crystalline arrangements and, therefore, might lead to the bias results. This assessment was confirmed as shown by graphs for the systems with no defects in Fig. 4.2-4.5

For the systems with one single vacancy defect, the different values were chosen for $n_{d}$ in each case. For system with the total atoms of $2000, n_{d}$ was 3 . The system with the total atoms of $6750, n_{d}$ was 7 . For the system with the total atoms of 16000, $n_{d}$ was 11, and the yalue of 15 was chosen for $n_{d}$ for the system with the total atoms of 31250
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Fig. 4.2 Variation of Average Atomic Volumes with Number of subsystems $\left(n_{d}\right)$; จุหาลงกรณมหาวิทยาลย


Fig. 4.4 Variation of Average Atomic Volumes with Number of subsystems $\left(n_{d}\right)$;
(c) system with initial 16000 atoms.


Fig. 4.5 Variation of Average Atomic Volumes with Number of subsystems $\left(n_{d}\right)$;

### 4.5 Transients of Single Vacancy Defects

With the values for $n_{d}$ as previously described, their transients were
simulated. Due to the very large number of atoms involved in the simulation and those complex movements, the change in the average atomic volume was chosen to represent the transient. The results as obtained were shown in Fig. 4.6

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Fig. 4.6 Change in Average Atomic Volume over Times due to single vacancy defect
of system with initial 2000 atoms 6750 atoms, 16000 atoms and 31250 atoms.
It was clearly seen for the cases of 2000 and 6750 initial atoms that the average atomic volumes were suddenly increased. This was due to the space left by the missing latom which allowed the neighbor atoms to expand. The average atomic volume then was gradually decreased as the neighboring atoms were expanding to fill such space. It was observed that the process was slower as the total initial atom was increased. Considering that the expanding was tikely caused by the repulsion between increased. Considering that the expanding was likely caused by the repulsion between
atoms, the longer transient period would suggest that there are the shielding effects that retard the expanding process.
vacancies were studied in system of 2000 atoms, which their vacancies atoms were 2 -,
3-, 4-, and 5- atoms. The transients of these systems were observed by choosing $n_{d}=$

3, and the change in the average atomic volume over time of single vacancy showed in
Fig. 4.7 to compare with multiple vacancies those were shown in Fig. 4.8-4.11.


Fig. 4.7 Change in Average Atomic Volume over Times due to single vacancy defect in
 volume was deēreased. The average atomic volume were alsöfound to be varied such that the more vacancies tended to result in the larger final average atomic volume

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Fig. 4.9 Change in Average Atomic Volume over Times due to 3-vacancies defect in
system with initial 2000 atoms.


Fig. 4.10 Change in Average Atomic Volume over Times due to 4-vacancies defect in ystem with initial 2000 atoms.


Fig. 4.11 Change in average atomic volume over times due to 5 -vacancies defect in
system with initial 2000 atoms.

## CHAPTER V

CONCLUSION AND SUGGESTION

### 5.1 Conclusion

The dissertation has studied the phenomena of the point defect transient via two models, the spring-mass model and the ALINE program.
 dynamics in simple cubic crystal/ by the Hamiltonian calculation in MD simulation method, and then use RK4 is implied as a numerical integrator. This model showed the conservation of Hamiltonian and the vibration of displaced atom over the run time 2000.

In addition, the dissertation has studied the phenomena of the point defect transient via running ALINE program. The study on the transient of the single vacancy defect in the crystalline medium of FCC type was conducted. Due to the range number of atoms and their complex movements, the change in the average atomic volume over time was used to indicate the process of transient.

While it was observed in general that the crystalline medium would expand and eventually fill in the space left by the defect, the actual time needed for the process and the actual size of the defect were not indicated and nalysed. Even though
the similar pattern of transients was to be expected, the effect of defect size and the time needed for transient process were still very crucial. The effect of the defect density and/or the size of the system to be simulated were also of concern and required further investigation, Even more important was how the type of atoms/ions that-formed basis of the crystalline structure affects the transient process. Further study in this regard was

### 5.2 Suggestions

1. The study should be conducted in other different phenomena of point defect, such as self-interstitials, or substitutional. Moreover, there should be extending results to other crystal systeml |)
2. There should be various forms of potential energy function that can represent the atomic interaction in molecular dynamic model, both of two-body interaction and multi-body interaetion.



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## Appendix A

Program A1: Spring-Mass model; Force calculation by formula method.




double e_k(double vxx, double vyy, double vzz) \{
return 0.5*MS*(vxx*vxx+vyy*vyy+vzz*vzz);
\}
/* function e_p
/* Calculate the potential energy by Harmonicl Potential */
double e_p(double xa, double xb, double ya, double yb, double za, double zb) \{
return $0.5^{*} \mathrm{~K}^{*}$ pow(sqrt(pow $((x a-x b), 2)+\square$

int i, nd3;
int mii, mjj, mkk, mill;
int ii, jj, kk;
int nl, nr;

nd3=nd3*3;
$E p=0.0 ;$
for $(i=0 ; i<n d 3 ; i++)\{$
$m 2 i j k(i, n d, \& m i i, \& m j j, \& m k k, \& m \|)$;

## จุฬาลงกाรณมหหาวิทยาลัย <br> $y r=y r i g h t(n r) ;$

$z r=z r i g h t(n r) ;$
n2ijk(nr,nd,\&ii,\&jj,\&kk);

case 0 :



```
f_z[n_r]=f_z[n_r]+cz;
f_z[n_l]=f_z[n_l]-cz;
```


## break;


int i, j, k, l, m, mii, mjj, mkk, mll, n, nd, n_left, n_right, nprint;

n2ijk(n, nd, \&i, \&j, \&k);

## จุหาลงกรณ์มหาวิทยาลัย <br> $z[n]=k^{* 1} 1.0 ;$

$v x[n]=0.0$;
$v y[n]=0.0 ;$

```
vz[n]=0.0;
```

\}
printf("Displaced atom no. : ");
scanf("\%d",\&d_a);
printf("displaced = ");
scanf("\%f",\&rd_a);
printf("filename : ");
scanf("\%s",filename);

FILE *spring;
spring=fopen(filename,"w"
d_n=d_a;
rd_n=rd_a;

fprintf(spring,"Displaced [\%d] from \%f \%f \%f ", d_n,x[d_n],y[d_n],z[d_n]);
$x\left[d \_n\right]=x\left[d \_n\right]+r d \_n ;$
$y\left[d \_n\right]=y\left[d \_n\right]+r d \_n$;


// Harmonic Potential

h0=ham(nd);
//printf("h0 = \%f $\operatorname{ln\backslash n",h0);~}$
//system("pause");
fprintf(spring,"h0= \%20.10f\n\n",h0);

$d y[0][n]=v y[n]^{*} d t ;$
$\left.\begin{array}{l}d v z[0][n]=a z[n]^{*} d t ; \\ d z[0][n]=v z[n]^{*} d t ;\end{array}\right) /(2)$


$\mathrm{fx}[\mathrm{n}]=0.0$;

if(nprint==100)\{
fprintf(spring,"\%5.2f \%15.10f \%15.10f",t,h0,hn);
fprintf(spring,"\%15.5f \%15.5f \%15.5fln",x[d_n],y[d_n],z[d_n]);


Program A2: Spring-Mass modet; Force calculation by numerical method.

\#define NDIM33 81000
\#define D 3
\#define RT 2000
//NDIM33 $=$ NDIM3*3 (spring storage in $x, y, z$ )
I/lattice size (for SC : $A^{*} A^{*} A$ )
//run time
/* INITIAL DATA :: SPRING, POSITION, VELOCITY */
double fx[NDIM3], fy[NDIM3], fz[NDIM3], ax[NDIM3], ay[NDIM3], az[NDIM3],
vx[NDIM3], vy[NDIM3], vz[NDIM3], x[NDIM3], y[NDIM3], z[NDIM3],
rx[NDIM3], ry[NDIM3], rz[NDIM3];
double $\times$ _O[NDIM3], y_O[NDIM3], $\quad$ z_O[NDIM3];
double dvx[4][NDIM3], dvy[4][NDIM3], dvz[4][NDIM3],

void m2ijkl(int mm, int ndd, int *mi/int *mj, int *mk, int *ml)
int ii,jj,kk,Il;
$k k=m m /\left(n d d^{*} n d d^{*} 3\right)$
$j j=\left(m m-k k^{*} n d d^{*} n d d^{*} 3\right) /\left(3^{*} n d d\right)$;
$\mathrm{ii}=\left(\mathrm{mm}-k k^{*} \mathrm{ndd}^{*} \mathrm{ndd}^{*} 3-\mathrm{j}{ }^{*}\right.$ ndd* 3$) / 3 ;(2) / 200$
II=mm-kk*ndd*ndd* $3-\mathrm{jj}^{*}$ * $n d d^{*} 3-\mathrm{ii}^{*} 3 ; 20.2$
*mi=ii;

/* Conveft 3D index for lattice to 1D index */

int N ;

void n2ijk(int nn, int ndd, int *ni, int *nj, int *nk)
\{
int iii,jjj,kkk;
$k k k=n n /\left(n d d^{*} n d d\right) ;$
jjj $=\left(n n-k k k^{*} n d d^{*} n d d\right) / n d d ;$
iii=nn-kkk*ndd*ndd-jjj*ndd;
*ni=iii;
*nj=jjj;
*nk=kkk;

```
}
```

/* find 1D index for the lattice connecter :: xleft
/* find 1D index for the lattice connected to the left side of the spring */
double xleft(int hright,int nleft) \{
return $x[n l e f t]$;
else

## if(nleft!=nright $+\left(\mathrm{D}^{*}(\mathrm{D}-1)\right)$ ) return $\mathrm{y}[\mathrm{nleft}]$; else <br> จุพาลงครณมมหาวิทยาลัย <br> double zleft(int nright,int nleft)

\{
if(nleft!=nright+(D*D*(D-1)))
return z[nleft];
else

```
        return -(D*L-z[nleft]);
```




pow((ya-yb),2)+
pow((za-zb),2))-L,2);
/*
function :: hamiltonian
double ham(int nd)
\{


if(ii<0)

## (4) $0+\begin{aligned} & \text { else } \operatorname{if}(m \|==1)\{ \\ & j j=j j-1 ; 0) \\ & i f(j j<0) j j=n d-1 ;\end{aligned}$

\} else \{
$k k=k k-1$;
if( $(\mathrm{kk}<0) \mathrm{kk}=\mathrm{nd}-1$;
\}
$n \mathrm{n}=\mathrm{ijk} 2 n(i i, j j, k k, n d)$;
$x|=x| e f t(n r, n l)$;

void coeff(double fnx[1], double fny[], double fnz[])
\{
double hh, hnewx, hnewy, hnewz;
int n ;

for $\left(n=0 ; n<D^{*} D^{*} D ; n^{+}+2 \underline{2}\right.$
$x[n]=x[n]+d r ; 0)$
nnewx=ham(D);
$f n x[n]=-(h n e w x-h h) / d r$;

## จุหาลงกรณมหาวิทยาลัย <br> hnewy=ham(D);

fny[n]=-(hnewy-hh)/dr;
$y[n]=r y[n] ;$

double time; // check running time; in ms. (divide CLOCK_PER_SEC to get in sec.)
runtime $=$ RT;
$n d=D ;$

d_n=d_a;
rd_n=rd_a;
fprintf(spring," $\operatorname{Displaced[\% d]~from~\% f~\% f~} \% f$ ", d_ $\left.n, x\left[d \_n\right], y\left[d \_n\right], z\left[d \_n\right]\right) ;$
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d_x=x[d_n];
$\mathrm{d} \_\mathrm{y}=\mathrm{y}\left[\mathrm{d} \_\mathrm{n}\right]$;
d_z=z[d_n];
fprintf(spring,"to \%f \%f \%fln\n",x[d_n],y[d_n],z[d_n]);



$x[n]=x \_0[n]+\left(d x[0][n]+2.0^{*} d x[1][n]+2.0^{*} d x[2][n]+d x[3][n]\right) / 6.0 ;$

\#define MXI 500
\#define MXJ 500
\#define MXK 500

double $x, y, z, d x, d y, d z ;$
double vspec_avg, total_count, sumsd, sd;


FILE *ofile;
maxdata $=0 ;$
$x m x=0.0$;


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ifile=fopen(filename,"r");
rfile=fopen(filenamer,"a+");

$d z=(z m x-z m n) / n d i v ;$
fprintf(rfile,"dx dy dz\n");
fprintf(rfile,"\%10.4If \%10.4If \%10.4If

fscanf(ifile,"\%d\%|f\%|f\%|f\%) \n",\&n,\&x,\&y,\&z);

$\}$ while(!feof(fifie) ):


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iff((count[i]>0) \&\& (i>0)) \{
fprintf(rfile,"\%5d \%10d \%10.4|fln",i,count[i],dx*dy*dz/i);
total_count=total_count+count[i];
vspec_avg=vspec_avg+dx*dy*dz/i*count[i];
\}
vspec_avg=vspec_avg/total_count;
fprintf(rfile,"\%10If \%10.4|f".total_count,_vspec_avg);


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## Appendix B

Procedure to run ALINE program



Fig. B2 Initial condition builder window appearing at the starting of the program.

9. Setting time to record the coordinate of each atom at the pull down menu 'Output' and select 'ANIMATION' as shown in Fig. B4.
10. At the main GUI, click 'RUN'.
11. For more information, please see reference no. [10].


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## Biography

## Ms. Kwuanchanok Chansawang was born on October 29, 1975 in

 Ubonratchathani, Thailand. She got her Bachelor degree from the Department of Agricultural Engineering, Faculty of Engineering, Khon Kaen University in 1998 and Master degree from-Department of Nuclear Technology, Faculty of Engineering, Chulalongkorn University in 2001. In Juhe 2005, she studied in the Doctoral degree at the Department of Nuclear Jechnology, Faculty of Engineering, Chulalongkorn University.

## ศูนย์วิทยทรัพยากร

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